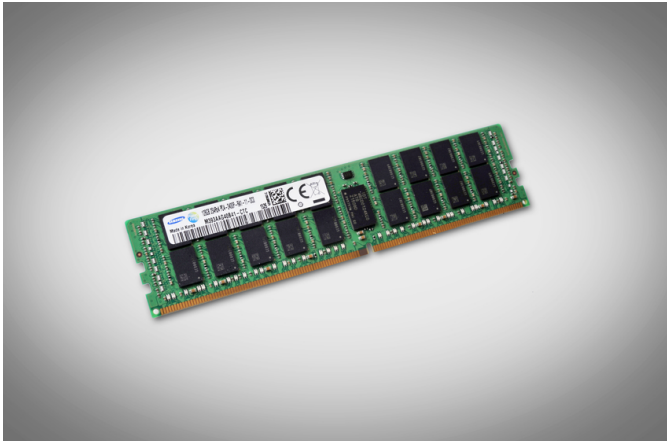


Samsung Produces 128GB Server TSV DRAM Modules

Written by Marco Attard
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Samsung mass produces what it says is the first through silicon via (TSV) DDR4 memory in 128GB modules designed for enterprise server and datacentre use.



An update on the 64GB TSV DDR4 DRAM modules introduced in 2014, the new Samsung TSV DRAM modules claim the largest capacity and highest neergy efficiency around, while offering high speeds and "excellent" reliability. Each 128GB TSV DDR4 RDIMM carries 144 DDR4 chips arranged into 36 4GB DRAM packages. Each package in turn contains four 20nm-based 8Gb chips assembled using TSV packaging technology.

TSV technology involves the grinding of chip dies down to a few dozen micrometers before piercing with hundreds of fine holes. Electrodes are then passed vertically through the holes, a process allowing for data transmission speeds of up to 2400Mbps.

"We are pleased that volume production of our high speed, low-power 128GB TSV DRAM module will enable our global IT customers and partners to launch a new generation of enterprise solutions with dramatically improved efficiency and scalability for their investment," Samsung says. "We will continue to expand our technical cooperation with global leaders in servers, consumer electronics and emerging markets, where consumers can benefit from innovative technology that enhances their productivity and the overall user experience."

The 128GB TSV DRAM modules should be available within the next few weeks. In addition, Samsung says it will present higher performance TSV DRAM products with data transfer speeds of up to 2667 and 3200Mbps.

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